2SC4533

Silicon NPN triple diffusion planar type

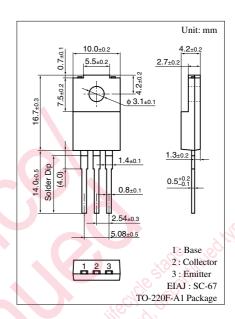
For high breakdown voltage high-speed switching

■ Features

- High-speed switching
- \bullet High collector to base voltage V_{CBO}
- Wide area of safe operation (ASO)
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25$ °C

| Symbol | Rating | Unit | |
|------------------|--|---|--|
| V _{CBO} | 500 | V | |
| V _{CES} | 500 | v | |
| V _{CEO} | 400 | V | |
| V _{EBO} | 7 | V | |
| I_{CP} | 6 | A | |
| $I_{\rm C}$ | 3 | A | |
| I_{B} | 1.2 | A | |
| P _C | 30 | W | |
| | 2 | | |
| T _j | 150 | °C | |
| T _{stg} | -55 to +150 | °C///0 | |
| | V _{CBO} V _{CES} V _{CEO} V _{EBO} I _{CP} I _C I _B P _C | V _{CBO} 500 V _{CES} 500 V _{CEO} 400 V _{EBO} 7 I _{CP} 6 I _C 3 I _B 1.2 P _C 30 2 T _j 150 | |

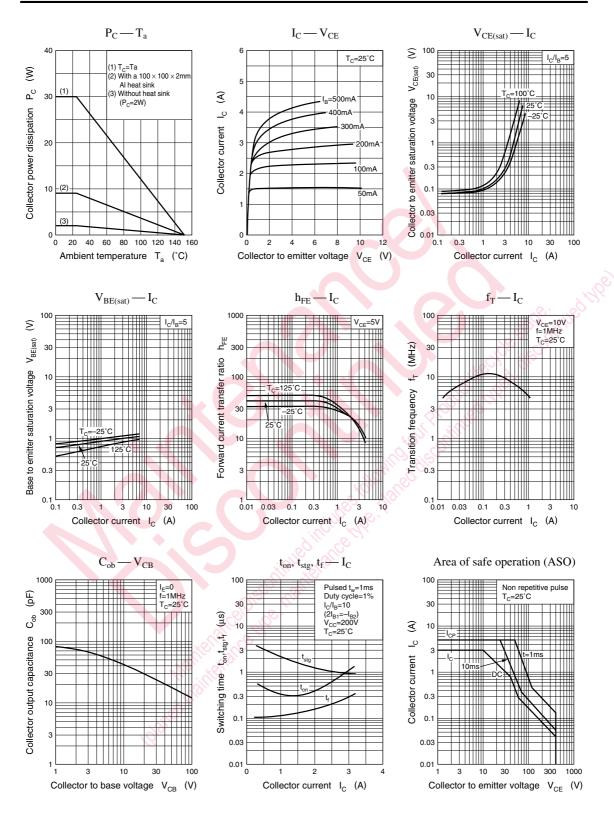


■ Electrical Characteristics $T_C = 25$ °C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|--|-----|-----|-----|------|
| Collector cutoff current | I _{CBO} | $V_{CB} = 500 \text{ V}, I_{E} = 0$ | | | 100 | μΑ |
| Emitter cutoff current | I _{EBO} | $V_{EB} = 5 \text{ V}, I_{C} = 0$ | | | 100 | μΑ |
| Collector to emitter voltage | V_{CEO} | $I_C = 10 \text{ mA}, I_B = 0$ | 400 | | | V |
| Forward current transfer ratio | h _{FE1} | $V_{CE} = 5 \text{ V}, I_{C} = 0.1 \text{ A}$ | 10 | | | |
| M | h _{FE2} | $V_{CE} = 2 \text{ V}, I_{C} = 1.2 \text{ A}$ | 8 | | 40 | |
| Collector to emitter saturation voltage | V _{CE(sat)} | $I_C = 1.5 \text{ A}, I_B = 0.3 \text{ A}$ | | | 1.0 | V |
| Base to emitter saturation voltage | V _{BE(sat)} | $I_C = 1.5 \text{ A}, I_B = 0.3 \text{ A}$ | | | 1.5 | V |
| Transition frequency | f_T | $V_{CE} = 10 \text{ V}, I_{C} = 0.2 \text{ A}, f = 1 \text{ MHz}$ | | 10 | | MHz |
| Turn-on time | t _{on} | $I_C = 1.5 \text{ A}, I_{B1} = 0.15 \text{ A}, I_{B2} = -0.3 \text{ A},$ | | | 1.0 | μs |
| Storage time | t _{stg} | $V_{CC} = 200 \text{ V}$ | | | 3.0 | μs |
| Fall time | $t_{\rm f}$ | | | | 0.3 | μs |

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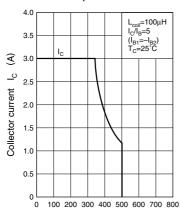
Power Transistors 2SC4533



Panasonic 233

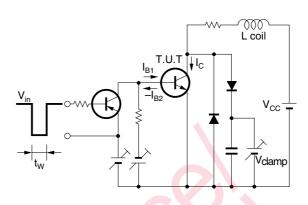
Power Transistors 2SC4533

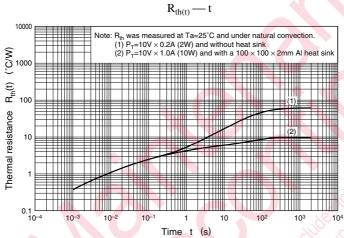
Area of safe operation, reverse bias ASO



Collector to emitter voltage V_{CE} (V)

Reverse bias ASO measuring circuit





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